

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (currently amended) A method of forming a multilayer dielectric film on a substrate, comprising the steps of:
forming a metal silicate layer on the surface of the substrate; ~~and~~
forming a metal oxide layer atop the metal silicate layer, said metal oxide layer being selected from the group of ZrO_2 and HfO_2 ; and
forming another metal silicate layer atop the metal oxide layer, wherein said metal silicate layers each have a dielectric constant lower than the metal oxide layer.

Please cancel claim 2

2. (cancelled).

3. (currently amended) The method of claim 1 ~~or 2~~ wherein said forming steps are carried out by any one of, or combination of, chemical vapor deposition (CVD), physical vapor deposition (PVD), atomic layer deposition (ALD), aerosol pyrolysis, spray coating or spin-on-coating.

4. (currently amended) The method of claim 1 ~~or 2~~ wherein said forming steps are carried out by chemical vapor deposition (CVD) and using an oxygen source selected from the group consisting of O_2 , O_3 , NO, N_2O , H_2O , OH^\cdot , alcohol, alkoxides, and H_2O_2 .

Please cancel claim 5.

5(cancelled).

6. (currently amended) The method of claim ~~5~~ 1 wherein said metal oxide layer has a dielectric constant in a range of 15 to 200 and said metal silicate layer has a dielectric constant in a range of 5 to 100.

Please cancel claim 7.

7(cancelled).

8. (original) The method of claim 7 wherein said metal oxide includes more than one metal element.

Please cancel claim 9

9.(cancelled)

10. (currently amended) The method of claim ~~5~~ 1 wherein said metal silicate has the formula of M_xSiO_y , where M is a metal selected from the group consisting of Zr, Hf, Ti, V, Nb, Ta, Cr, Mo, W, Mn, Zn, Al, Ga, In, Ge, Sr, Pb, Sb, Bi, Sc, Y, La, Be, Mg, Ca, Sr, Ba, Th, Lanthanides (Ce, Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu), and mixtures thereof, x is a number in the range of 1 to 3, and y is a number in the range of 2 to 5.

11. (original) The method of claim 10 wherein said metal silicate includes more than one metal element.

12. (original) The method of claim 10 wherein said metal silicate is selected from the group consisting of Zr-Si-O and Hf-Si-O.

13. (currently amended) The method of claim 1 ~~or 2~~ wherein said metal silicate layer has a thickness smaller than a thickness of said metal oxide.

Appl. No. 10/766,618
Reply to Office Action of May 4, 2005

14. (original) The method of claim 13 wherein said metal oxide layer has a thickness in a range of about 30 to 80Å.

15. (original) The method of claim 13 wherein said second metal silicate layer has a thickness of one to two atomic layers.